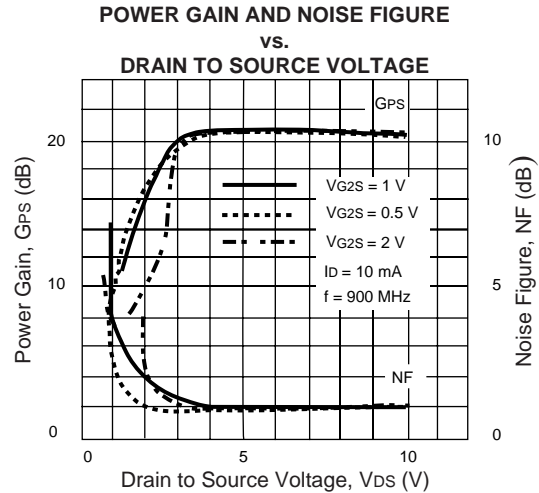


FEATURES

- SUITABLE FOR USE AS RF AMPLIFIER IN UHF TUNER
- LOW C_{RSS} : 0.02 pF (TYP)
- HIGH POWER GAIN: 20 dB (TYP) AT 900 MHz
- LOW NF: 1.1 dB TYP AT 900 MHz
- $L_{G1} = 1.0 \mu\text{m}$, $L_{G2} = 1.5 \mu\text{m}$, $W_G = 400 \mu\text{m}$
- ION IMPLANTATION
- AVAILABLE IN TAPE & REEL OR BULK
- LOW PACKAGE HEIGHT: 1.0 mm MAX

DESCRIPTION

The NE25118 is a dual gate GaAs FET designed to provide flexibility in its application as a mixer, AGC amplifier, or low noise amplifier. As an example, by shorting the second gate to the source, higher gain can be realized than with single gate MESFETs. This device is available in a 4 pin super mini-mold package, (SOT-343 type). Maximum package height of 1.0 mm makes the NE25118 an ideal device for PCMCIA card applications.



ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

PART NUMBER PACKAGE OUTLINE			NE25118 18		
SYMBOL	PARAMETERS AND CONDITIONS	UNITS	MIN	TYP	MAX
NF	Noise Figure at $V_{DS} = 5 \text{ V}$, $V_{G2S} = 1 \text{ V}$, $I_D = 10 \text{ mA}$, $f = 900 \text{ MHz}$	dB		1.1	2.5
GPS	Power Gain at $V_{DS} = 5 \text{ V}$, $V_{G2S} = 1 \text{ V}$, $I_D = 10 \text{ mA}$, $f = 900 \text{ MHz}$	dB	16	20	
BV_{DSX}	Drain to Source Breakdown Voltage at $V_{G1S} = -4 \text{ V}$, $V_{G2S} = 0$, $I_D = 10 \mu\text{A}$	V	13		
I_{DSS}	Saturated Drain Current at $V_{DS} = 5 \text{ V}$, $V_{G2S} = 0 \text{ V}$, $V_{G1S} = 0 \text{ V}$	mA	5	20	40
$V_{G1S}(\text{OFF})$	Gate 1 to Source Cutoff Voltage at $V_{DS} = 5 \text{ V}$, $V_{G2S} = 0 \text{ V}$, $I_D = 100 \mu\text{A}$	V	-3.5		
$V_{G2S}(\text{OFF})$	Gate 2 to Source Cutoff Voltage at $V_{DS} = 5 \text{ V}$, $V_{G1S} = 0 \text{ V}$, $I_D = 100 \mu\text{A}$	V	-3.5		
I_{G1SS}	Gate 1 Reverse Current at $V_{DS} = 0$, $V_{G1S} = -4 \text{ V}$, $V_{G2S} = 0$	μA			10
I_{G2SS}	Gate 2 Reverse Current at $V_{DS} = 0$, $V_{G2S} = -4 \text{ V}$, $V_{G1S} = 0$	μA			10
$ Y_{FS} $	Forward Transfer Admittance at $V_{DS} = 5 \text{ V}$, $V_{G2S} = 1 \text{ V}$, $I_D = 10 \text{ mA}$, $f = 1.0 \text{ kHz}$	mS	18	25	35
C_{ISS}	Input Capacitance at $V_{DS} = 5 \text{ V}$, $V_{G2S} = 1 \text{ V}$, $I_D = 10 \text{ mA}$, $f = 1 \text{ MHz}$	pF	0.5	1.0	1.5
C_{RSS}	Reverse Transfer Capacitance at $V_{DS} = 5 \text{ V}$, $V_{G2S} = 1 \text{ V}$, $I_D = 10 \text{ mA}$, $f = 1 \text{ MHz}$	pF		0.02	0.03

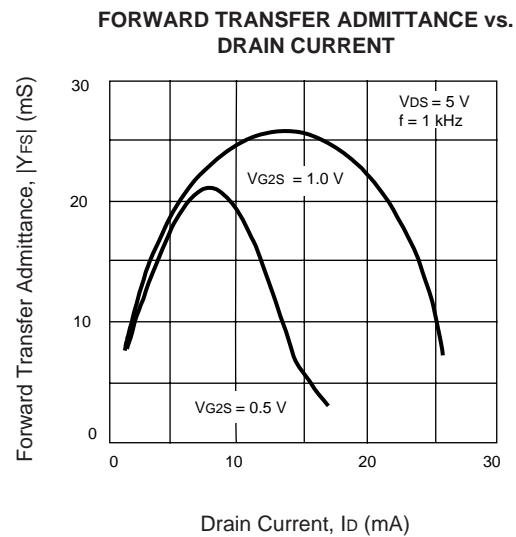
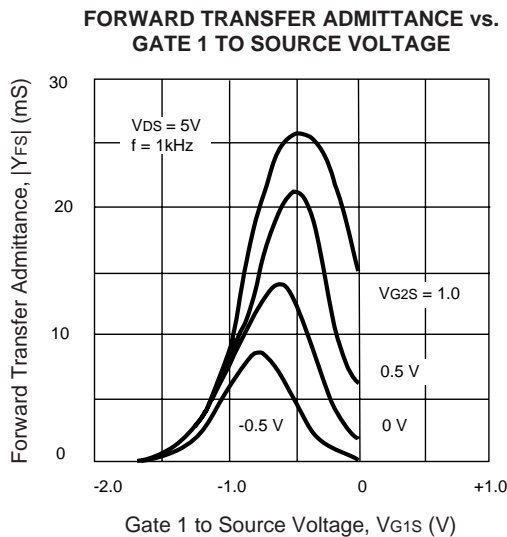
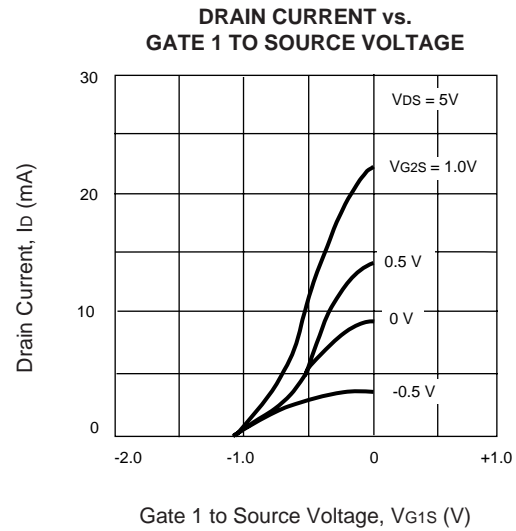
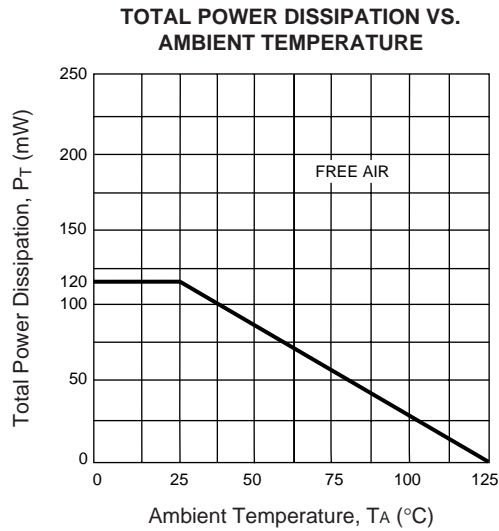
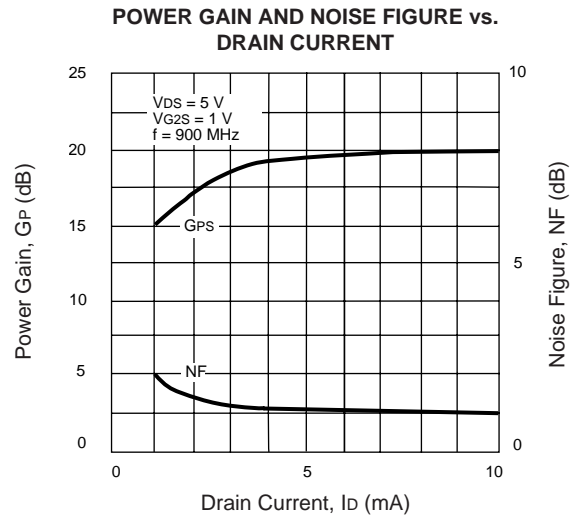
ABSOLUTE MAXIMUM RATINGS¹ (T_A = 25°C)

SYMBOLS	PARAMETERS	UNITS	RATINGS
V _{DS}	Drain to Source Voltage	V	13
V _{G1S}	Gate 1 to Source Voltage	V	-4.5
V _{G2S}	Gate 2 to Source Voltage	V	-4.5
I _D	Drain Current	mA	I _{DSS}
P _T	Total Power Dissipation	mW	120
T _{CH}	Channel Temperature	°C	125
T _{STG}	Storage Temperature	°C	-55 to +125

Note:

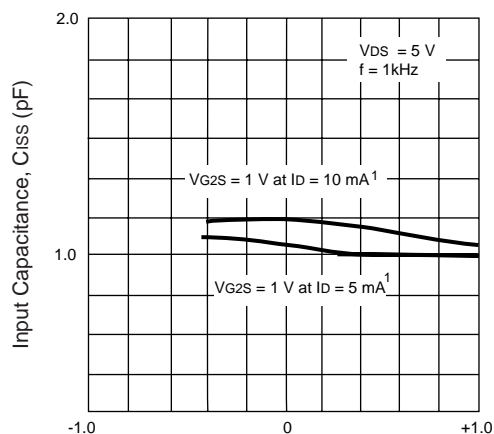
1. Operation in excess of anyone of these parameters may result in permanent damage.

TYPICAL PERFORMANCE CURVES (T_A = 25 °C)



TYPICAL PERFORMANCE CURVES (T_A = 25°C)

**INPUT CAPACITANCE vs.
GATE 2 TO SOURCE VOLTAGE**

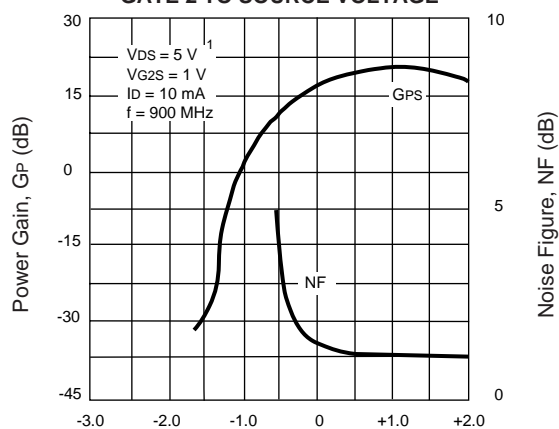


Gate 2 to Source Voltage, VG2S (V)

Note:

1. Initial bias conditions. VG1S set to obtain specified drain current.

**POWER GAIN AND NOISE FIGURE
vs.
GATE 2 TO SOURCE VOLTAGE**



Gate 2 to Source Voltage, VG2S (V)

Note:

1. Initial bias conditions. VG1S set to obtain specified drain current.

NE25118

V_{DS} = 5 V, V_{GS} = 1 V, I_D = 10 mA

FREQUENCY (MHz)	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
100	0.999	-3.3	2.359	177.2	0.006	-122.3	0.969	-1.3
200	1.000	-7.2	2.389	169.3	0.004	123.0	0.981	-2.9
300	0.998	-9.3	2.313	164.4	0.000	-145.0	0.979	-3.3
400	0.974	-13.4	2.233	160.0	0.004	79.2	0.967	5.6
500	1.005	-15.7	2.420	158.4	0.007	29.7	0.999	-5.8
600	0.942	-19.1	2.300	150.0	0.003	65.0	0.958	-7.7
700	0.968	-22.2	2.332	145.5	0.004	45.5	0.997	-8.5
800	0.920	-25.2	2.229	141.5	0.008	80.1	0.957	-9.4
900	0.952	-28.9	2.447	136.8	0.004	8.3	0.999	-12.5
1000	0.898	-29.4	2.303	131.1	0.001	50.9	0.968	-11.1
1100	0.915	-35.1	2.348	125.8	0.004	71.4	0.984	-14.8
1200	0.879	-35.2	2.367	123.5	0.000	91.1	0.989	-13.0

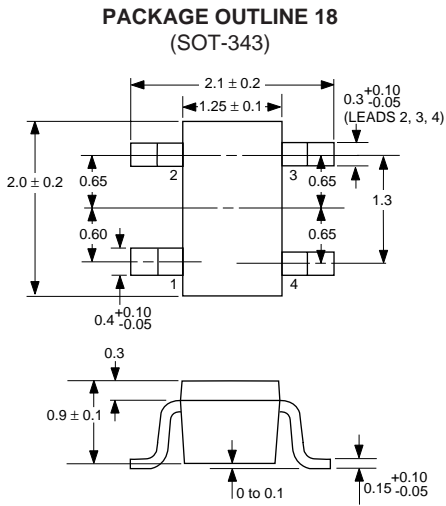
Note:

1. Gain Calculations:

$$\text{MAG} = \frac{|S_{21}|}{|S_{12}|} \left(K \pm \sqrt{K^2 - 1} \right). \text{ When } K \leq 1, \text{ MAG is undefined and MSG values are used. } \text{MSG} = \frac{|S_{21}|}{|S_{12}|}, K = \frac{1 + |\Delta|^2 - |S_{11}|^2 - |S_{22}|^2}{2 |S_{12} S_{21}|}, \Delta = S_{11} S_{22} - S_{21} S_{12}$$

MAG = Maximum Available Gain, MSG = Maximum Stable Gain

OUTLINE DIMENSIONS (Units in mm)



PIN CONNECTIONS

- 1. Source
- 2. Drain
- 3. Gate 2
- 4. Gate 1

Note: All dimensions are typical unless otherwise specified.

ORDERING INFORMATION

PART NUMBER	AVAILABILITY
NE25118	Bulk up to 3K
NE25118-T1	3K/Reel